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Stocking Distributor

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[Vishay/Siliconix](#)
[SI4890DY-T1-E3](#)

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sales@integrated-circuit.com



Si4890DY
Vishay Siliconix

N-Channel Reduced Q_g , Fast Switching MOSFET

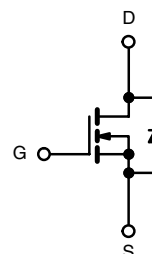
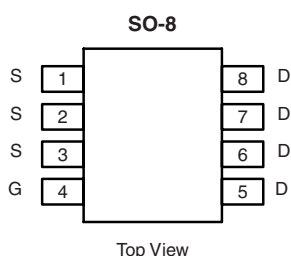
PRODUCT SUMMARY		
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
30	0.012 at $V_{GS} = 10$ V	± 11
	0.020 at $V_{GS} = 4.5$ V	± 9

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFETs
- High-Efficiency PWM Optimized
- Compliant to RoHS Directive 2002/95/EC



RoHS
COMPLIANT
HALOGEN
FREE
Available



N-Channel MOSFET

Ordering Information: Si4890DY-T1-E3 (Lead (Pb)-free)
 Si4890DY-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 25	
Continuous Drain Current ($T_J = 150$ °C) ^{a, b}	I_D	$T_A = 25$ °C	± 11
		$T_A = 70$ °C	± 9
Pulsed Drain Current (10 μ s Pulse Width)	I_{DM}	± 50	A
Continuous Source Current (Diode Conduction) ^{a, b}	I_S	2.3	
Maximum Power Dissipation ^{a, b}	P_D	$T_A = 25$ °C	2.5
		$T_A = 70$ °C	1.6
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient (MOSFET) ^a	R_{thJA}		50	°C/W
		$t \leq 10$ s	70	
		Steady State		

Notes:

a. Surface Mounted on FR4 board.

b. $t \leq 10$ s.

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MOSFET SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	0.8			V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\ \text{V}, V_{GS} = \pm 20\ \text{V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 24\ \text{V}, V_{GS} = 0\ \text{V}$			1	μA
		$V_{DS} = 24\ \text{V}, V_{GS} = 0\ \text{V}, T_J = 55\text{ }^\circ\text{C}$			5	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\ \text{V}, V_{GS} = 10\ \text{V}$	40			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\ \text{V}, I_D = 11\ \text{A}$		0.0098	0.012	Ω
		$V_{GS} = 4.5\ \text{V}, I_D = 9\ \text{A}$		0.0164	0.020	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15\ \text{V}, I_D = 11\ \text{A}$		21		S
Diode Forward Voltage ^a	V_{SD}	$I_S = 2.3\ \text{A}, V_{GS} = 0\ \text{V}$		0.71	1.1	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = 15\ \text{V}, V_{GS} = 5.0\ \text{V}, I_D = 11\ \text{A}$		14.2	20	nC
Gate-Source Charge	Q_{gs}			3.3		
Gate-Drain Charge	Q_{gd}			6.6		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\ \text{V}, R_L = 15\ \Omega$ $I_D \cong 1\ \text{A}, V_{GEN} = 10\ \text{V}, R_g = 6\ \Omega$		13	20	ns
Rise Time	t_r			8.5	15	
Turn-Off Delay Time	$t_{d(off)}$			35	53	
Fall Time	t_f			17	26	
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = 2.3\ \text{A}, di/dt = 100\ \text{A}/\mu\text{s}$		35	70	

Notes:

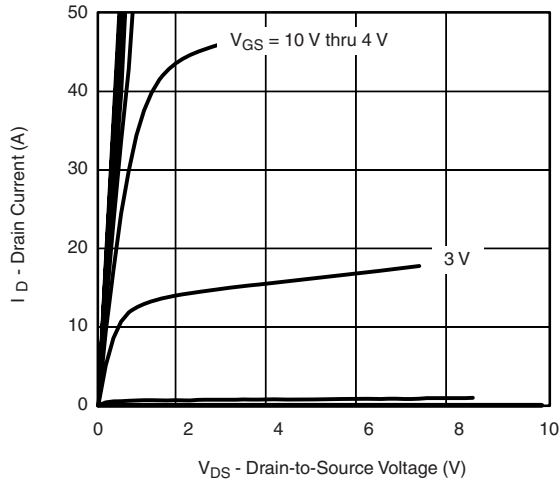
- a. Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

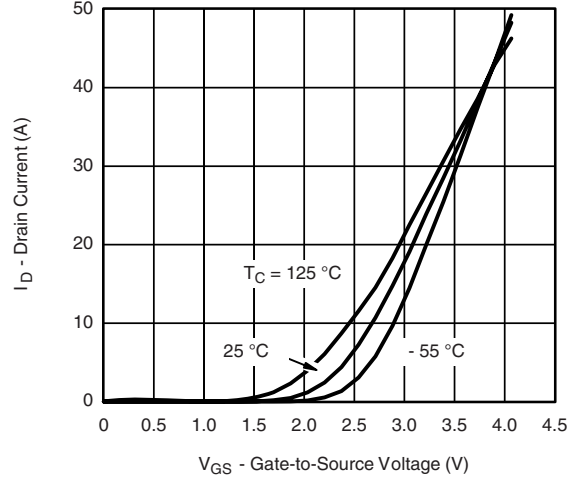


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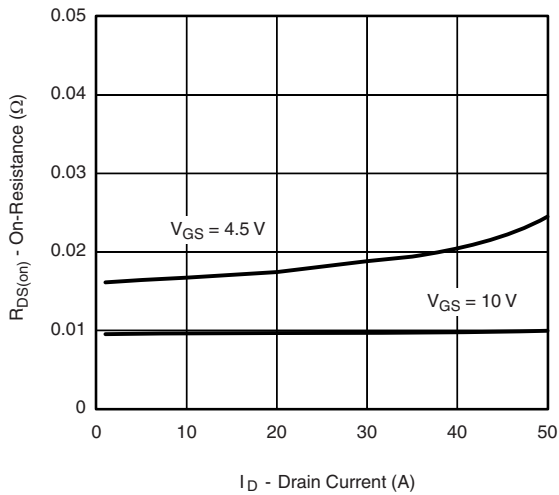
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



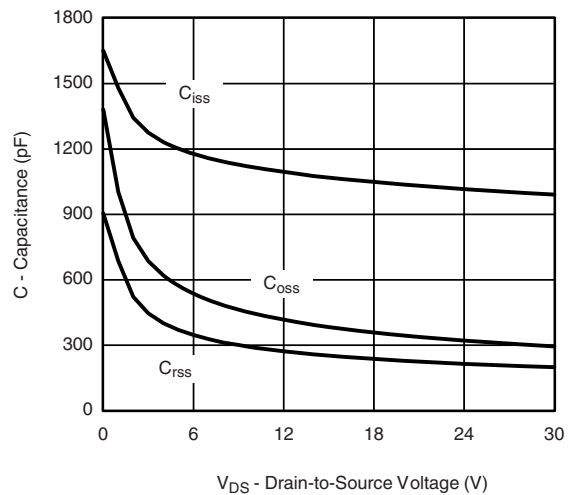
Output Characteristics



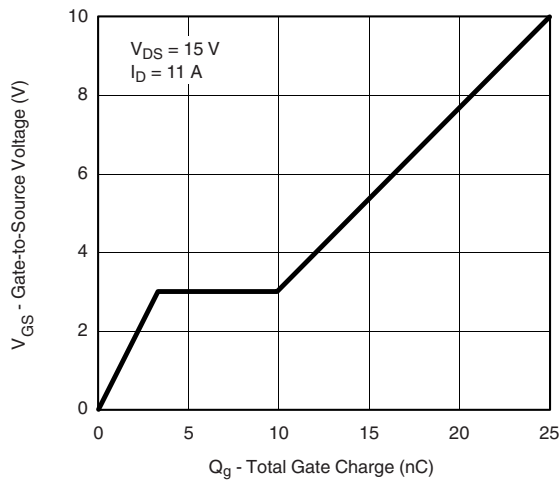
Transfer Characteristics



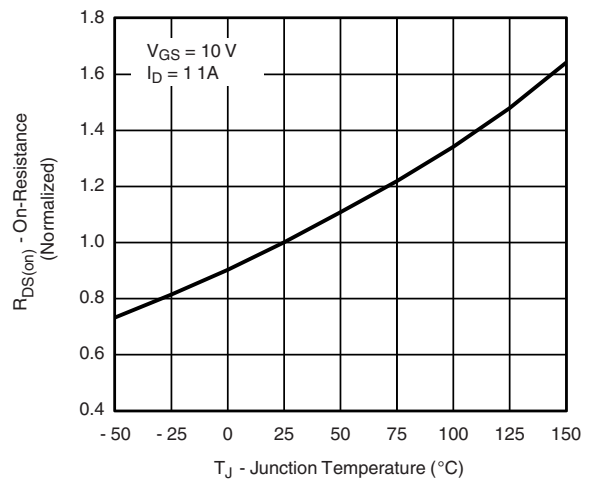
On-Resistance vs. Drain Current



Capacitance



Gate Charge



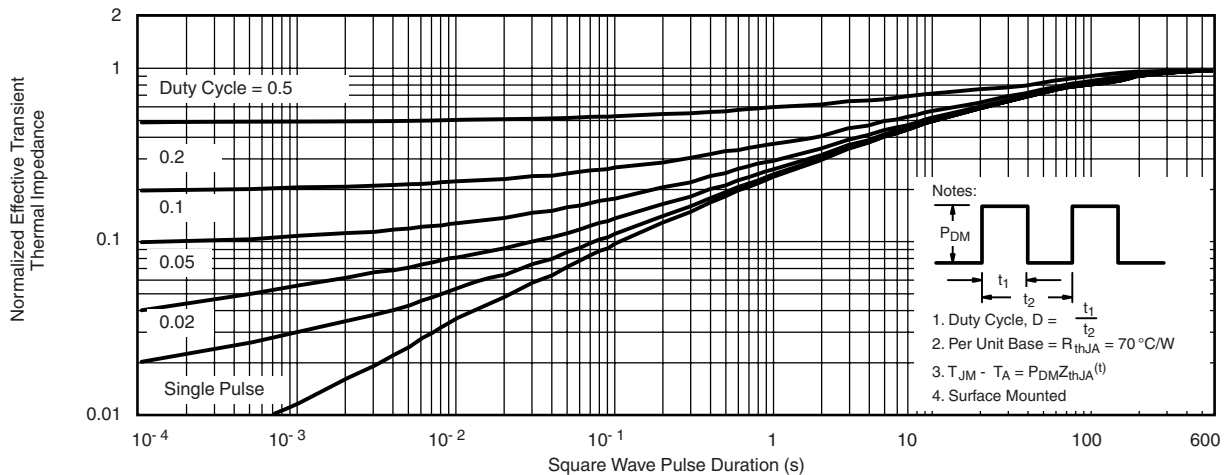
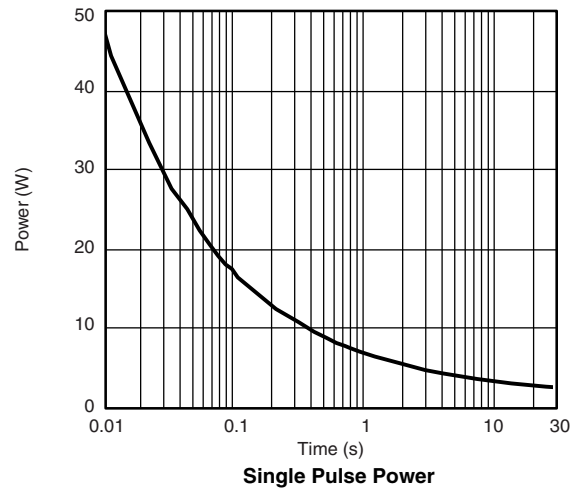
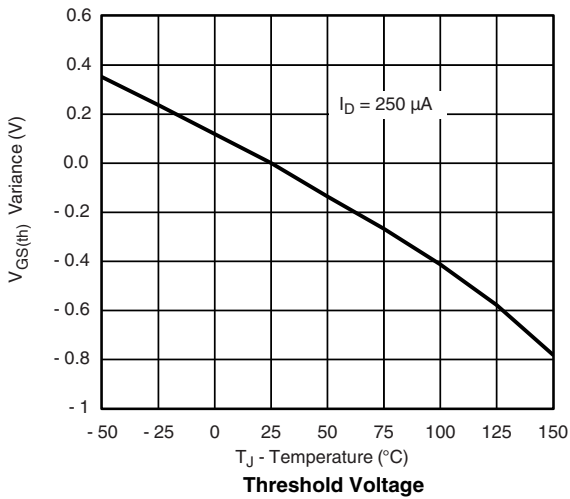
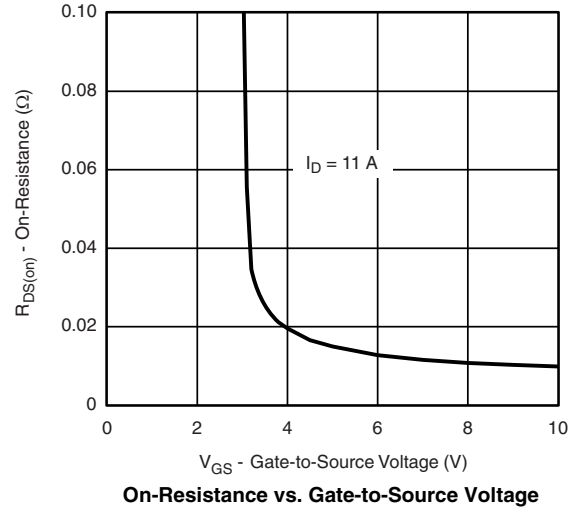
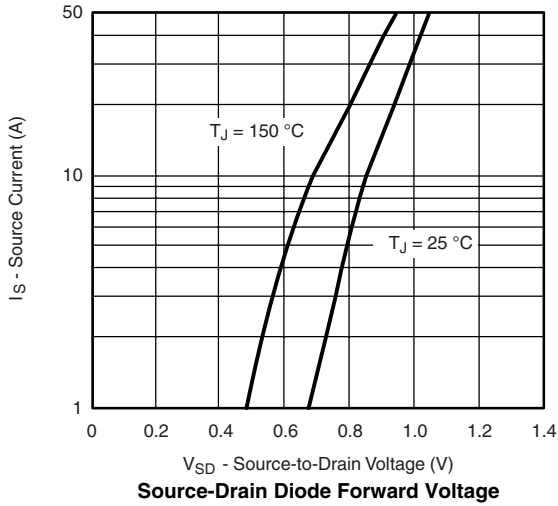
On-Resistance vs. Junction Temperature

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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?70855.

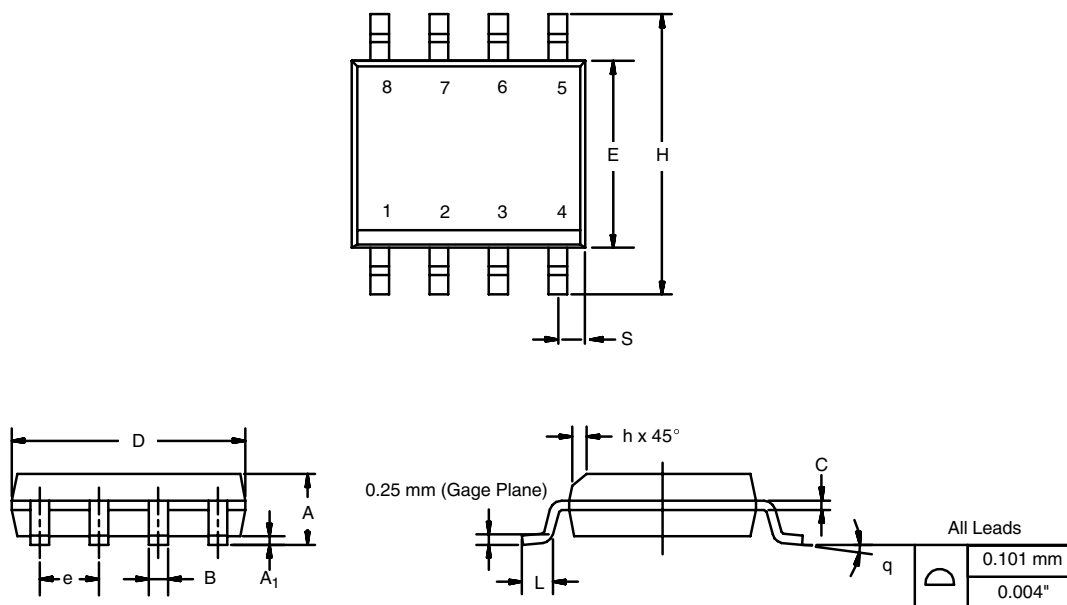


Package Information

Vishay Siliconix

SOIC (NARROW): 8-LEAD

JEDEC Part Number: MS-012



DIM	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A ₁	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°
S	0.44	0.64	0.018	0.026

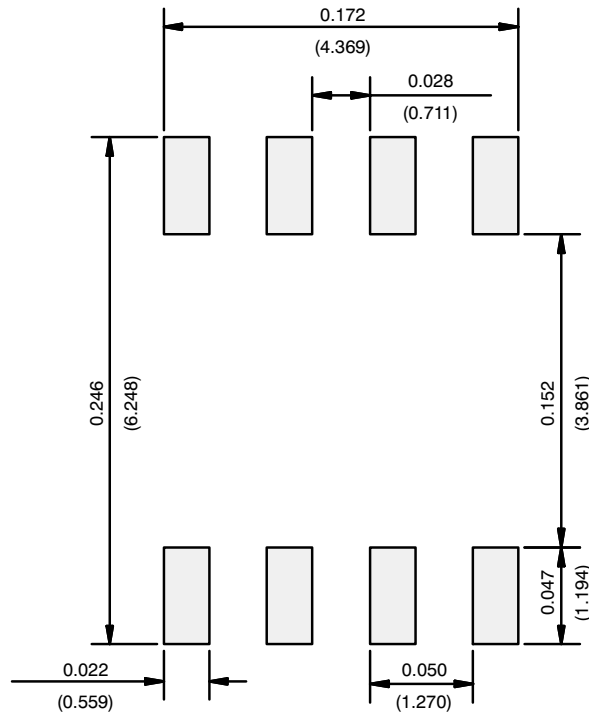
ECN: C-06527-Rev. I, 11-Sep-06
DWG: 5498

Application Note 826

Vishay Siliconix



RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads
 Dimensions in Inches/(mm)

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APPLICATION NOTE



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